

IN THE CLAIMS

This listing of the claims will replace all prior versions, and listings of claims in the application.

Listings of Claims:

1. (Currently Amended) A semiconductor device comprising:
a plurality of IC chips that are connected each other by wiring and disposed on a substrate; ~~wherein said~~ each IC chip is being connected to outside said substrate by input wiring and output wiring; and
at least one a-transistor element that is disposed in series with said connecting wiring between said IC chips and has a nominal resistance value, and said at least one transistor element that serves as an operation checking switch for said each correspondingly connected IC chip, is inserted in series into said wiring connecting between said IC chips, and
a compensation circuit that is electrically connected to said at least one transistor element and operable to automatically compensate for variations from said nominal resistance value.
2. (Currently Amended) The semiconductor device according to claim 1, wherein said at least one transistor element serves as a damping resistor.
3. (Currently Amended) The semiconductor device according to claim 1, ~~wherein~~ further comprising a termination resistance that is formed-disposed in parallel with on said connecting wiring connecting between said IC chips and grounded.
4. (Currently Amended) The semiconductor device according to claim 1, wherein said at least one transistor element is a depletion mode FET.
5. (Cancelled).
6. (Currently Amended) The semiconductor device according to claim 3, wherein said termination resistance and said ~~resistance-automatic-compensation circuit~~ are electrically connected.

7. (Original) The semiconductor device according to claim 1, wherein said substrate is a silicon substrate.

8. (Original) The semiconductor device according to claim 1, wherein said substrate is a glass substrate.

9. (New) A semiconductor device comprising:
a plurality of IC chips that are connected each other by wiring and disposed on a substrate, each IC chip being connected to outside said substrate by input wiring and output wiring,
at least one transistor element that is disposed in series with said connecting wiring between said IC chips and has nominal resistance value, and said at least one transistor serving as an operation checking switch for each correspondingly connected IC chip,
a compensation circuit that is electrically connected to said at least transistor element and operable to automatically compensate for variations from said nominal resistance value, and
a termination resistance that is disposed in parallel with said connecting wiring between said IC chips and grounded, and said termination being electrically connected to said compensation circuit.

10. (New) The semiconductor device according to claim 9, wherein said at least one transistor element serves as a damping resistor.

11. (New) The semiconductor device according to claim 9, wherein said at least one transistor element is a depletion mode FET.

12. (New) The semiconductor device according to claim 9, wherein said substrate is a silicon substrate.

13. (New) The semiconductor device according to claim 9, wherein said substrate is a glass substrate.